

**TOSHIBA**

TK7P60W

MOSFETs Silicon N-Channel MOS (DTMOSIV)

# TK7P60W

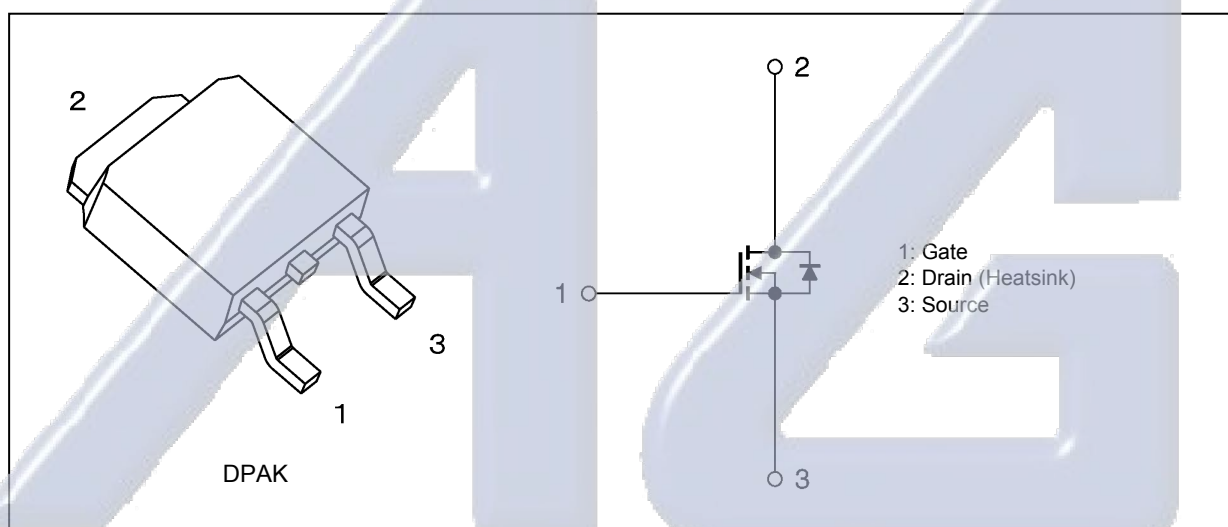
## 1. Applications

- Switching Voltage Regulators

## 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.5 \Omega$  (typ.)  
by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode:  $V_{th} = 2.7$  to  $3.7$  V ( $V_{DS} = 10$  V,  $I_D = 0.35$  mA)

## 3. Packaging and Internal Circuit



## 4. Absolute Maximum Ratings (Note) ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

| Characteristics                                | Symbol    | Rating     | Unit             |
|------------------------------------------------|-----------|------------|------------------|
| Drain-source voltage                           | $V_{DS}$  | 600        | V                |
| Gate-source voltage                            | $V_{GS}$  | $\pm 30$   |                  |
| Drain current (DC)                             | $I_D$     | 7.0        | A                |
| Drain current (pulsed)                         | $I_{DP}$  | 28         |                  |
| Power dissipation ( $T_c = 25^\circ\text{C}$ ) | $P_D$     | 60         | W                |
| Single-pulse avalanche energy                  | $E_{AS}$  | 92         | mJ               |
| Avalanche current                              | $I_{AR}$  | 1.8        | A                |
| Reverse drain current (DC)                     | $I_{DR}$  | 7.0        |                  |
| Reverse drain current (pulsed)                 | $I_{DRP}$ | 28         |                  |
| Channel temperature                            | $T_{ch}$  | 150        | $^\circ\text{C}$ |
| Storage temperature                            | $T_{stg}$ | -55 to 150 |                  |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics                    | Symbol         | Max  | Unit |
|------------------------------------|----------------|------|------|
| Channel-to-case thermal resistance | $R_{th(ch-c)}$ | 2.09 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.  
Note 2:  $V_{DD} = 90\text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial),  $L = 49.9\text{ mH}$ ,  $R_G = 25\text{ }\Omega$ ,  $I_{AR} = 1.8\text{ A}$

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



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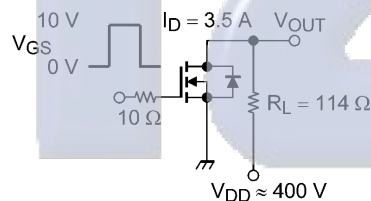
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**6. Electrical Characteristics****6.1. Static Characteristics ( $T_a = 25^\circ\text{C}$  unless otherwise specified)**

| Characteristics                | Symbol        | Test Condition                                     | Min | Typ. | Max     | Unit          |
|--------------------------------|---------------|----------------------------------------------------|-----|------|---------|---------------|
| Gate leakage current           | $I_{GSS}$     | $V_{GS} = \pm 30\text{ V}$ , $V_{DS} = 0\text{ V}$ | —   | —    | $\pm 1$ | $\mu\text{A}$ |
| Drain cut-off current          | $I_{DSS}$     | $V_{DS} = 600\text{ V}$ , $V_{GS} = 0\text{ V}$    | —   | —    | 10      |               |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $I_D = 10\text{ mA}$ , $V_{GS} = 0\text{ V}$       | 600 | —    | —       | V             |
| Gate threshold voltage         | $V_{th}$      | $V_{DS} = 10\text{ V}$ , $I_D = 0.35\text{ mA}$    | 2.7 | —    | 3.7     |               |
| Drain-source on-resistance     | $R_{DS(ON)}$  | $V_{GS} = 10\text{ V}$ , $I_D = 3.5\text{ A}$      | —   | 0.5  | 0.6     | $\Omega$      |

**6.2. Dynamic Characteristics ( $T_a = 25^\circ\text{C}$  unless otherwise specified)**

| Characteristics                | Symbol      | Test Condition                                                       | Min | Typ. | Max | Unit     |
|--------------------------------|-------------|----------------------------------------------------------------------|-----|------|-----|----------|
| Input capacitance              | $C_{iss}$   | $V_{DS} = 300\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$ | —   | 490  | —   | pF       |
| Reverse transfer capacitance   | $C_{rss}$   |                                                                      | —   | 1.7  | —   |          |
| Output capacitance             | $C_{oss}$   |                                                                      | —   | 13   | —   |          |
| Effective output capacitance   | $C_{o(er)}$ | $V_{DS} = 0\text{ to }400\text{ V}$ , $V_{GS} = 0\text{ V}$          | —   | 21   | —   |          |
| Gate resistance                | $r_g$       | $V_{DS} = \text{OPEN}$ , $f = 1\text{ MHz}$                          | —   | 7.0  | —   | $\Omega$ |
| Switching time (rise time)     | $t_r$       | See Figure 6.2.1                                                     | —   | 18   | —   | ns       |
| Switching time (turn-on time)  | $t_{on}$    |                                                                      | —   | 40   | —   |          |
| Switching time (fall time)     | $t_f$       |                                                                      | —   | 7.0  | —   |          |
| Switching time (turn-off time) | $t_{off}$   |                                                                      | —   | 55   | —   |          |
| MOSFET dv/dt ruggedness        | dv/dt       | $V_{DD} = 0\text{ to }400\text{ V}$ , $I_D = 3.5\text{ A}$           | 25  | —    | —   | V/ns     |

Duty  $\leq 1\%$ ,  $t_w = 10\text{ }\mu\text{s}$ **Fig. 6.2.1 Switching Time Test Circuit****6.3. Gate Charge Characteristics ( $T_a = 25^\circ\text{C}$  unless otherwise specified)**

| Characteristics                                 | Symbol    | Test Condition                                                                | Min | Typ. | Max | Unit |
|-------------------------------------------------|-----------|-------------------------------------------------------------------------------|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | $Q_g$     | $V_{DD} \approx 400\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 7.0\text{ A}$ | —   | 15   | —   | nC   |
| Gate-source charge 1                            | $Q_{gs1}$ |                                                                               | —   | 3.2  | —   |      |
| Gate-drain charge                               | $Q_{gd}$  |                                                                               | —   | 8.0  | —   |      |

**6.4. Source-Drain Characteristics ( $T_a = 25^\circ\text{C}$  unless otherwise specified)**

| Characteristics               | Symbol    | Test Condition                                                                              | Min | Typ. | Max  | Unit          |
|-------------------------------|-----------|---------------------------------------------------------------------------------------------|-----|------|------|---------------|
| Diode forward voltage         | $V_{DSF}$ | $I_{DR} = 7.0\text{ A}$ , $V_{GS} = 0\text{ V}$                                             | —   | —    | -1.7 | V             |
| Reverse recovery time         | $t_{rr}$  | $I_{DR} = 3.5\text{ A}$ , $V_{GS} = 0\text{ V}$<br>$-dI_{DR}/dt = 100\text{ A}/\mu\text{s}$ | —   | 230  | —    | ns            |
| Reverse recovery charge       | $Q_{rr}$  |                                                                                             | —   | 1.7  | —    | $\mu\text{C}$ |
| Peak reverse recovery current | $I_{rr}$  |                                                                                             | —   | 16   | —    | A             |
| Diode dv/dt ruggedness        | dv/dt     | $I_{DR} = 3.5\text{ A}$ , $V_{GS} = 0\text{ V}$ , $V_{DD} = 400\text{ V}$                   | 15  | —    | —    | V/ns          |

## 7. Marking

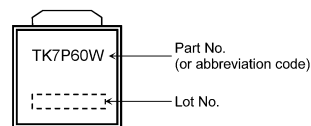


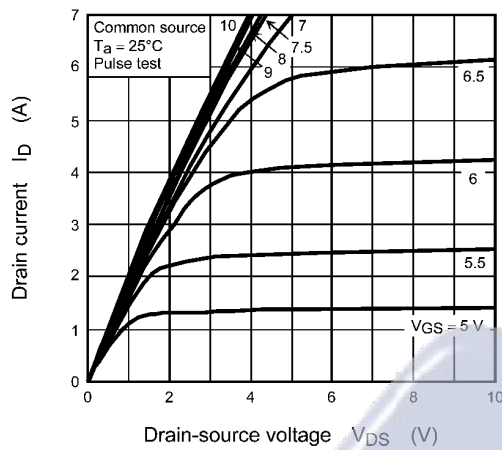
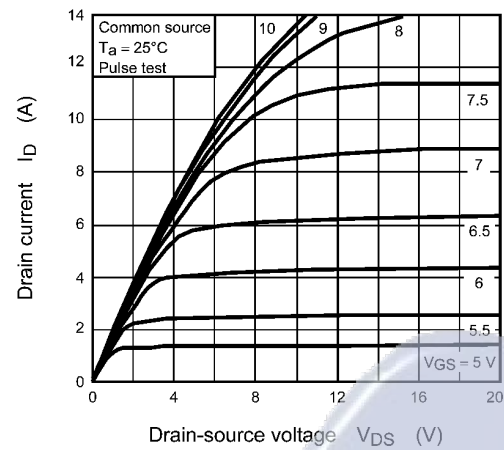
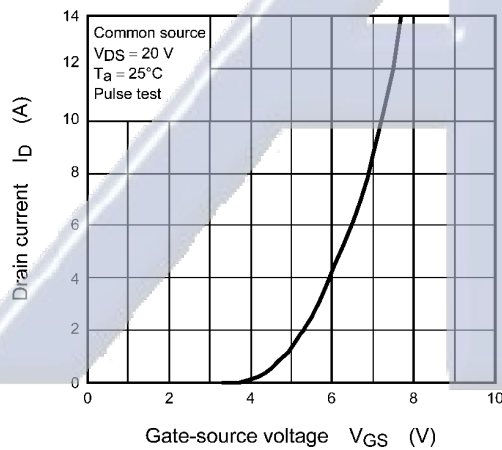
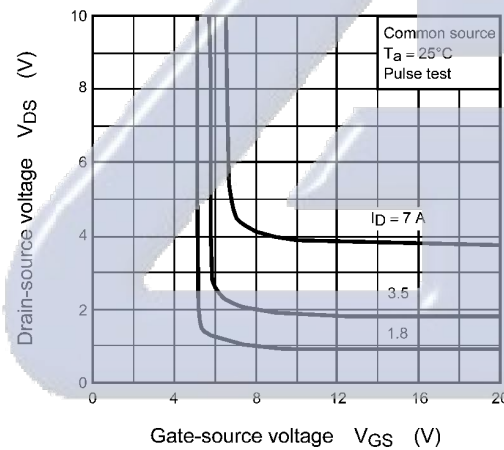
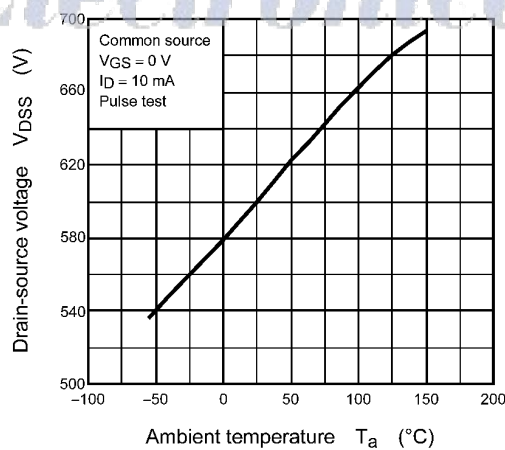
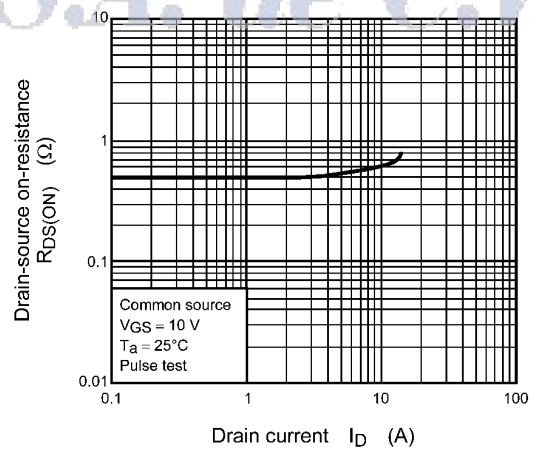
Fig. 7.1 Marking

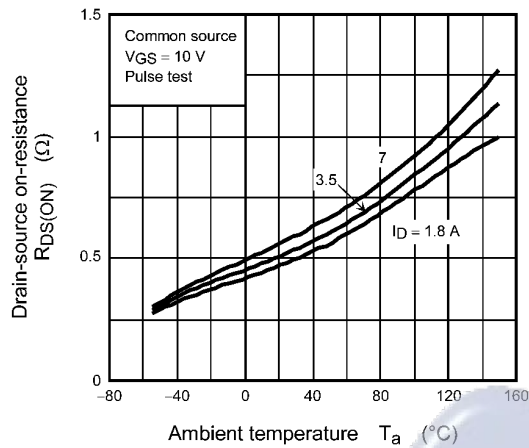
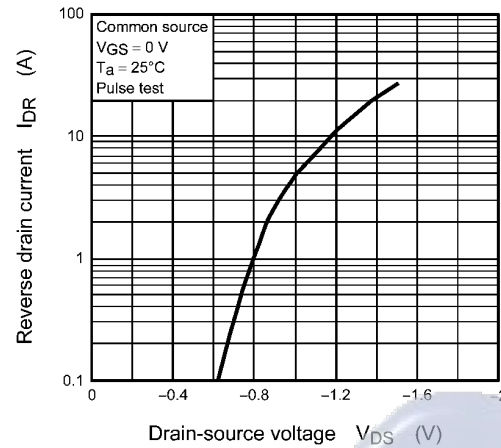
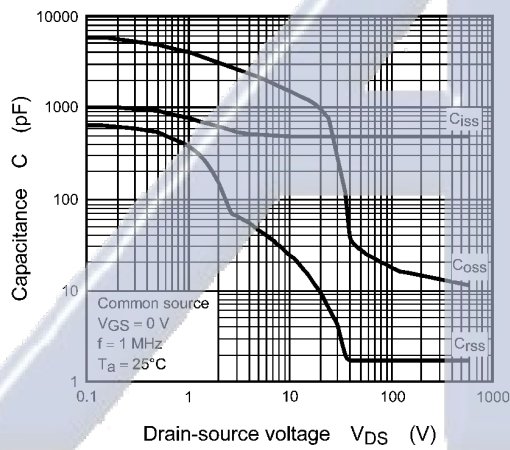
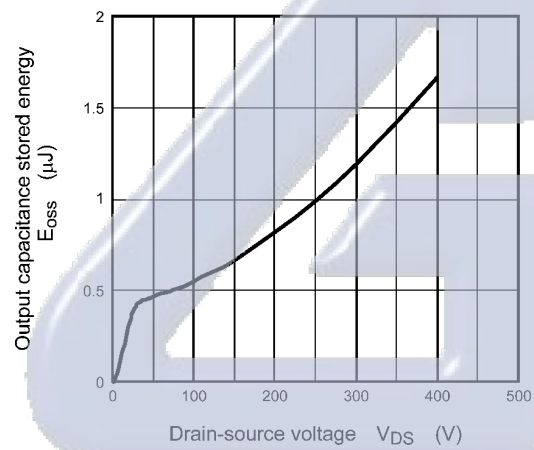
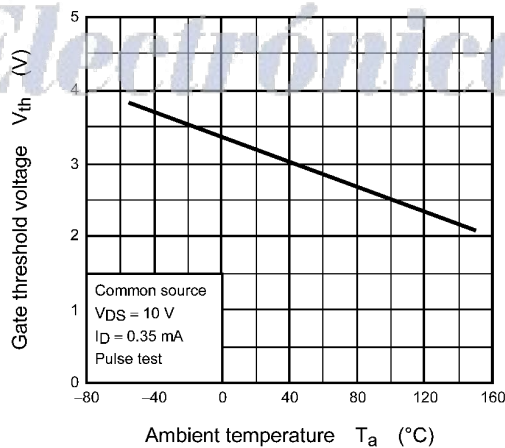
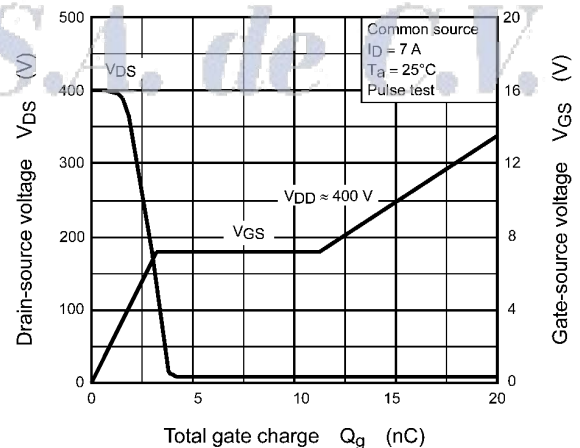
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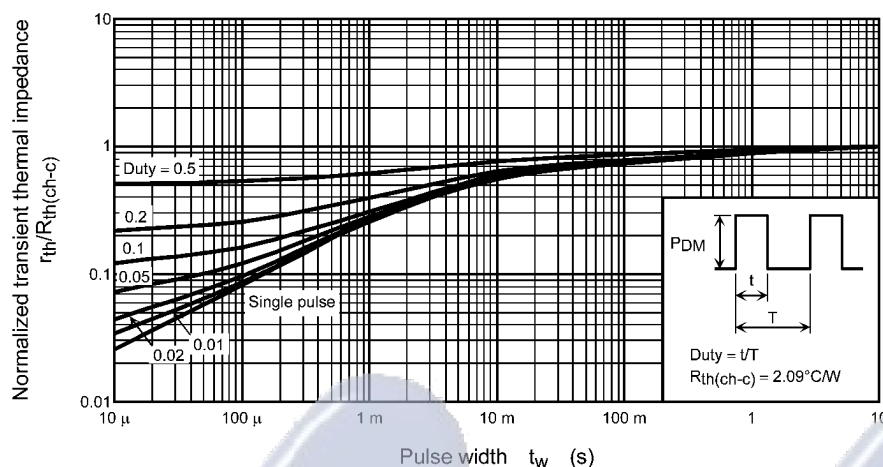
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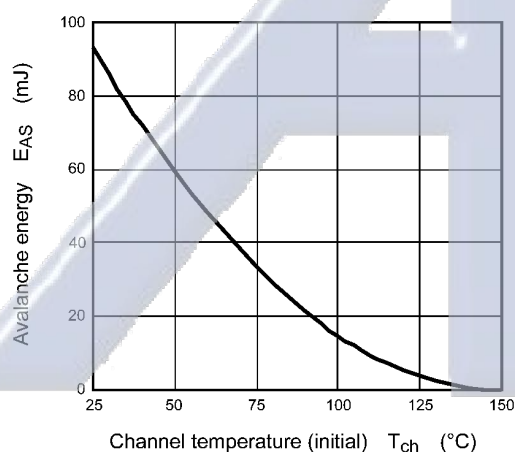
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**8. Characteristics Curves (Note)****Fig. 8.1  $I_D - V_{DS}$** **Fig. 8.2  $I_D - V_{DS}$** **Fig. 8.3  $I_D - V_{GS}$** **Fig. 8.4  $V_{DS} - V_{GS}$** **Fig. 8.5  $V_{DS} - T_a$** **Fig. 8.6  $R_{DS(ON)} - I_D$**

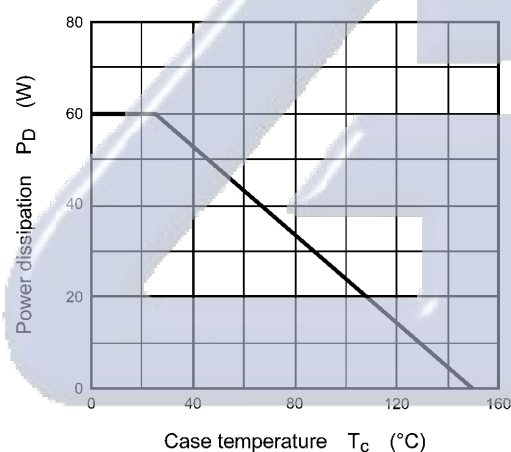
**Fig. 8.7  $R_{DS(ON)} - T_a$** **Fig. 8.8  $I_{DR} - V_{DS}$** **Fig. 8.9  $C - V_{DS}$** **Fig. 8.10  $E_{oss} - V_{DS}$** **Fig. 8.11  $V_{th} - T_a$** **Fig. 8.12 Dynamic Input/Output Characteristics**



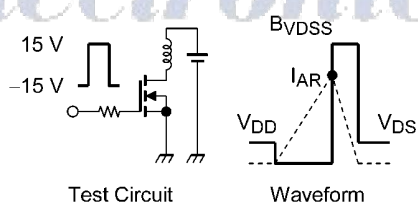
**Fig. 8.13  $r_{th} - t_w$**   
(Guaranteed Maximum)



**Fig. 8.14  $E_{AS} - T_{ch}$**   
(Guaranteed Maximum)

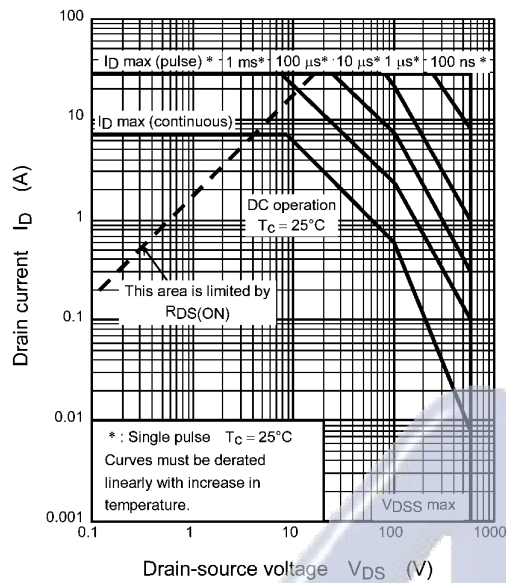


**Fig. 8.15  $P_D - T_c$**   
(Guaranteed Maximum)



$$R_G = 25 \, \Omega, V_{DD} = 90 \, \text{V} \quad E_{AS} = \frac{1}{2} \cdot L \cdot I_{AR}^2 \cdot \left( \frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

**Fig. 8.16 Test Circuit/Waveform**



**Fig. 8.17 Safe Operating Area  
(Guaranteed Maximum)**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

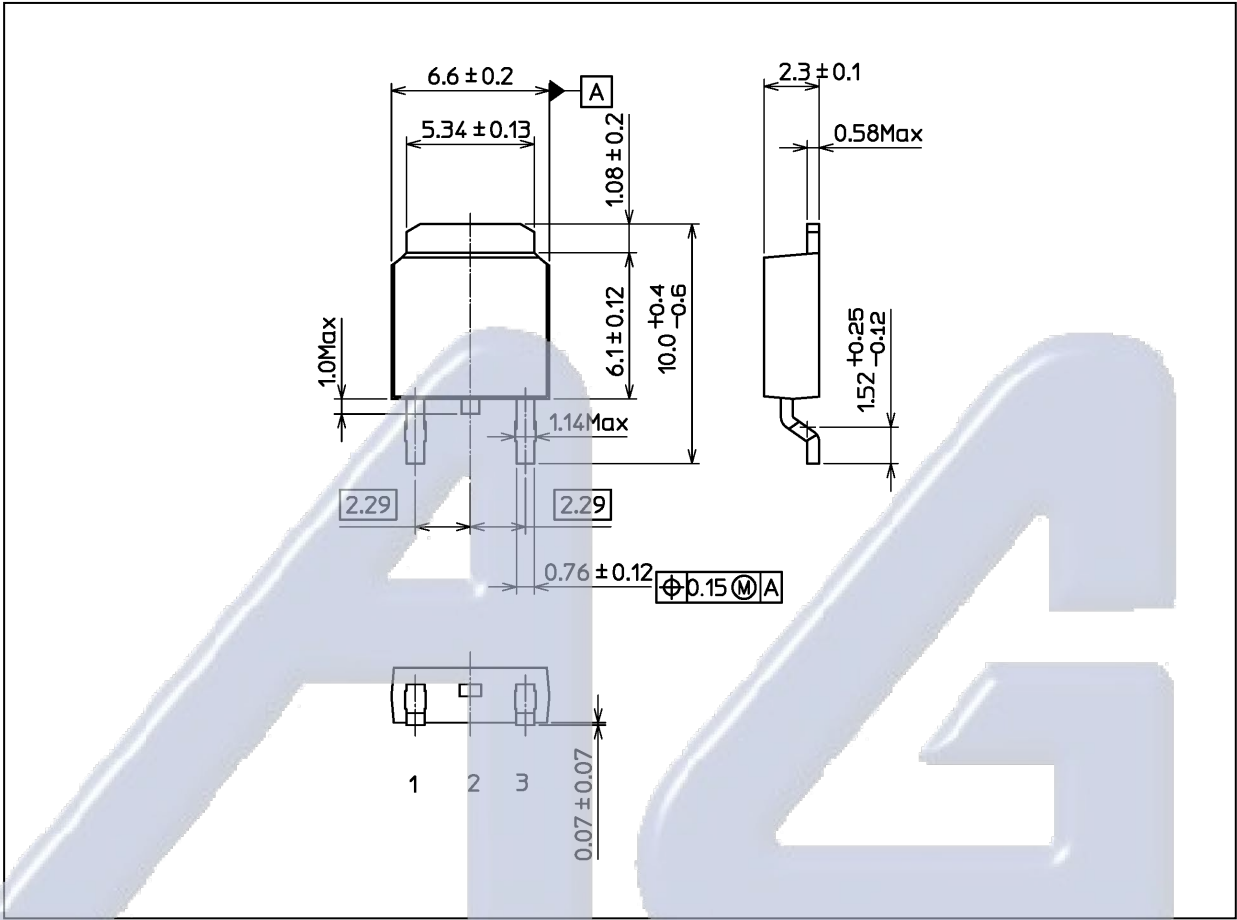
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TOSHIBA

TK7P60W

Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

| Package Name(s) |
|-----------------|
| TOSHIBA: 2-7K1S |
| Nickname: DPAK  |